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Thin Solid Films 267 (1995) 139

thin solid films

Author Index of Volume 267

Alferov, Zh.I., 32
Andrukhiv, A., 126
Andrukhiv, M., 126

Bąk-Misiuk, J., 74
Bauer, G., 15
Bergman, J.P., 84
Bimberg, D., 32
Bochkariova, L., 126
Bugajski, M., 84
Buslaps, T., 69

Crump, P.A., 106

Dobaczewski, L., 79
Dobrowolski, W., 79
Dvoretsky, S.A., 121
Dynowska, E., 74

Eaves, L., 106

Fedorenko, A.I., 134
Fedorov, A.G., 134
Frank, N., 15

Gallagher, B.L., 106
Godlewski, M., 84
Grodzicka, E., 79
Grundmann, M., 32
Guziewicz, E., 69

Hagston, W.E., 47
Hayden, R.K., 106
Henini, M., 106
Herman, M.A., 1, 114
Heydenreich, J., 32

Janik, E., 69, 74
Jaroszyński, J., 79
Johnson, R.L., 69

Kafader, U., 89
Kaniewska, M., 84
Karczewski, G., 64, 69, 74, 79
Khlyap, G., 126
Konarski, P., 114
Kopalko, K., 64
Kop'ev, P.S., 32
Kossut, J., 58, 64, 69, 74, 79
Kowalski, B.J., 69
Kozhukhov, A.V., 114

Kucharczyk, R., 129
Kutrowski, M., 64

Ledentsov, N.N., 32
Lee, E.Y., 89
Leszczyński, M., 74
Liberman, V.I., 121
Lubyshev, D.I., 51, 54

Mazurek, P., 95
Mikhailov, N.N., 121
Mikołajczak, P., 95
Mironov, O.A., 134
Monemar, B., 84
Muszalski, J., 51, 54

Németh, Š., 47

Obodnikov, V.I., 114
Orłowski, B.A., 69
Ovtchinnikov, A., 99

Papajová, D., 47
Paprocki, K., 95
Pessa, M., 99
Preobrazhenskii, V.V., 51, 54

Regiński, K., 51, 54, 84
Richter, U., 32
Rodgers, P.J., 106
Ruvimov, S.S., 32

Sasaki, A., 24
Sidorov, Yu.G., 121
Sipatov, A.Yu., 134
Sirringhaus, H., 89
Sitter, H., 37, 47
Springholz, G., 15
Szuszkiewicz, W., 74

Tappura, K., 99

Ustinov, V.M., 32

Van Gemmeren, T., 69
Varavin, V.S., 121
Veselý, M., 47
Von Känel, H., 89

Werner, P., 32
Wojtowicz, T., 64, 69, 74, 79

Zakrzewski, A.K., 74, 79

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Thin Solid Films 267 (1995) 140–141

thin solid films

Subject Index of Volume 267

Adsorption
MBE growth mechanisms; studies by Monte-Carlo simulation, 37

Band structure
growth and characterization of p-type GaAs/(AlGa)As heterostructures grown on high-index GaAs surfaces, 106
electronic surface states in a semi-infinite effective-mass superlattice, 129

Cadmium telluride
approaches to understanding MBE growth phenomena, 1
growth and characterization of quantum structures of diluted magnetic semiconductors, 58
luminescence study of $CdTe/Cd_{1-x}Mn_xTe$ quantum wells grown by MBE, 64
properties of epitaxially grown CdTe layers doped with indium, 79
the controlled growth of high-quality mercury cadmium telluride, 121
Computer simulation
a study of a kinetic rate equation model for simulations of MBE crystal growth: a comparison with Monte Carlo simulations, 47
Conductivity
properties of epitaxially grown CdTe layers doped with indium, 79

Deposition process
MBE growth mechanisms; studies by Monte-Carlo simulation, 37
Depth profiling
morphology of the InAlAs/InP interface in the MBE-grown heterostructures analysed by SIMS depth profiling, 114

Gallium arsenide
the effect of the MBE growth rate on the surface phase diagram for GaAs (001), 51
static phase diagrams of reconstructions for MBE-grown GaAs(001) and AlAs(001) surfaces, 54
exciton dynamics in thin AlGaAs/GaAs quantum wells grown by MBE, 84
GaInAsP gas-source MBE technology, 99
growth and characterization of p-type GaAs/(AlGa)As heterostructures grown on high-index GaAs surfaces, 106
Growth mechanism
approaches to understanding MBE growth phenomena, 1
MBE growth mechanisms; studies by Monte-Carlo simulation, 37
epitaxial silicides: new results from RHEED analysis, 95

Heterostructures
islands and critical thickness of InAs grown by MBE on nominally- and misoriented GaAs substrates, 24
self-organization processes in MBE-grown quantum dot structures, 32
exciton dynamics in thin AlGaAs/GaAs quantum wells grown by MBE, 84
the controlled growth of high-quality mercury cadmium telluride, 121
quasi-two-dimensional electron layer in ZnCdHgTe and PbS heterostructures, 126
High energy electron diffraction
epitaxial silicides: new results from RHEED analysis, 95

Indium arsenide
islands and critical thickness of InAs grown by MBE on nominally- and misoriented GaAs substrates, 24
self-organization processes in MBE-grown quantum dot structures, 32
Indium phosphide
GaInAsP gas-source MBE technology, 99
Interfaces
epitaxial metal silicides: interface mapping by scanning probe techniques, 89

Lattice parameters
structural properties of cubic MnTe layers grown by MBE, 74
Lead telluride
approaches to understanding MBE growth phenomena, 1
the origin of surface roughening in lattice-mismatched Frank van der Merwe type heteroepitaxy, 15
the epitaxial growth of IV–VI heterostructures and superlattices on (001)Si, 134
Luminescence
islands and critical thickness of InAs grown by MBE on nominally- and misoriented GaAs substrates, 24
luminescence study of $CdTe/Cd_{1-x}Mn_xTe$ quantum wells grown by MBE, 64
exciton dynamics in thin AlGaAs/GaAs quantum wells grown by MBE, 84

Magnetic properties and measurements
growth and characterization of quantum structures of diluted magnetic semiconductors, 58
Mercury telluride
the controlled growth of high-quality mercury cadmium telluride, 121
Molecular beam epitaxy
approaches to understanding MBE growth phenomena, 1
islands and critical thickness of InAs grown by MBE on nominally- and misoriented GaAs substrates, 24
a study of a kinetic rate equation model for simulations of MBE crystal growth: a comparison with Monte Carlo simulations, 47
the effect of the MBE growth rate on the surface phase diagram for GaAs (001), 51

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static phase diagrams of reconstructions for MBE-grown GaAs(001) and AlAs(001) surfaces, 54
growth and characterization of quantum structures of diluted magnetic semiconductors, 58
luminescence study of CdTe/$Cd_{1-x}Mn_xTe$ quantum wells grown by MBE, 64
structural properties of cubic MnTe layers grown by MBE, 74
properties of epitaxially grown CdTe layers doped with indium, 79
exciton dynamics in thin AlGaAs/GaAs quantum wells grown by MBE, 84
GaInAsP gas-source MBE technology, 99
growth and characterization of p-type GaAs/(AlGa)As heterostructures grown on high-index GaAs surfaces, 106
the controlled growth of high-quality mercury cadmium telluride, 121

Nanostructures
self-organization processes in MBE-grown quantum dot structures, 32
Nucleation
MBE growth mechanisms; studies by Monte-Carlo simulation, 37

Optical spectroscopy
growth and characterization of quantum structures of diluted magnetic semiconductors, 58
band structure of MBE-grown ZB-MnTe/CdTe–optical and photoemission studies, 69

Photoelectron spectroscopy
band structure of MBE-grown ZB-MnTe/CdTe–optical and photoemission studies, 69

Quantum effects
self-organization processes in MBE-grown quantum dot structures, 32
luminescence study of CdTe/$Cd_{1-x}Mn_xTe$ quantum wells grown by MBE, 64
epitaxial metal silicides: interface mapping by scanning probe techniques, 89

Raman scattering
structural properties of cubic MnTe layers grown by MBE, 74

Scanning tunnelling microscopy
the origin of surface roughening in lattice-mismatched Frank van der Merwe type heteroepitaxy, 15
epitaxial metal silicides: interface mapping by scanning probe techniques, 89
Schottky barrier
properties of epitaxially grown CdTe layers doped with indium, 79
quasi-two-dimensional electron layer in ZnCdHgTe and PbS heterostructures, 126
Secondary ion mass spectrometry
morphology of the InAlAs/InP interface in the MBE-grown heterostructures analysed by SIMS depth profiling, 114
Semiconductors
band structure of MBE-grown ZB-MnTe/CdTe–optical and photoemission studies, 69
GaInAsP gas-source MBE technology, 99
quasi-two-dimensional electron layer in ZnCdHgTe and PbS heterostructures, 126
Silicides
epitaxial metal silicides: interface mapping by scanning probe techniques, 89
epitaxial silicides: new results from RHEED analysis, 95
Silicon
the epitaxial growth of IV–VI heterostructures and superlattices on (001)Si, 134
Superlattices
electronic surface states in a semi-infinite effective-mass superlattice, 129
Surface and interface states
quasi-two-dimensional electron layer in ZnCdHgTe and PbS heterostructures, 126
electronic surface states in a semi-infinite effective-mass superlattice, 129
Surface morphology
the origin of surface roughening in lattice-mismatched Frank van der Merwe type heteroepitaxy, 15
a study of a kinetic rate equation model for simulations of MBE crystal growth: a comparison with Monte Carlo simulations, 47
morphology of the InAlAs/InP interface in the MBE-grown heterostructures analysed by SIMS depth profiling, 114
Surface roughness
the origin of surface roughening in lattice-mismatched Frank van der Merwe type heteroepitaxy, 15
morphology of the InAlAs/InP interface in the MBE-grown heterostructures analysed by SIMS depth profiling, 114
Surface structure
the effect of the MBE growth rate on the surface phase diagram for GaAs (001), 51
static phase diagrams of reconstructions for MBE-grown GaAs(001) and AlAs(001) surfaces, 54
epitaxial silicides: new results from RHEED analysis, 95

Transmission electron microscopy
the epitaxial growth of IV–VI heterostructures and superlattices on (001)Si, 134
Tunnelling
growth and characterization of p-type GaAs/(AlGa)As heterostructures grown on high-index GaAs surfaces, 106

X-ray diffraction
structural properties of cubic MnTe layers grown by MBE, 74
the epitaxial growth of IV–VI heterostructures and superlattices on (001)Si, 134

Yttrium
electronic surface states in a semi-infinite effective-mass superlattice, 129